

097695-070304
092070-59269250

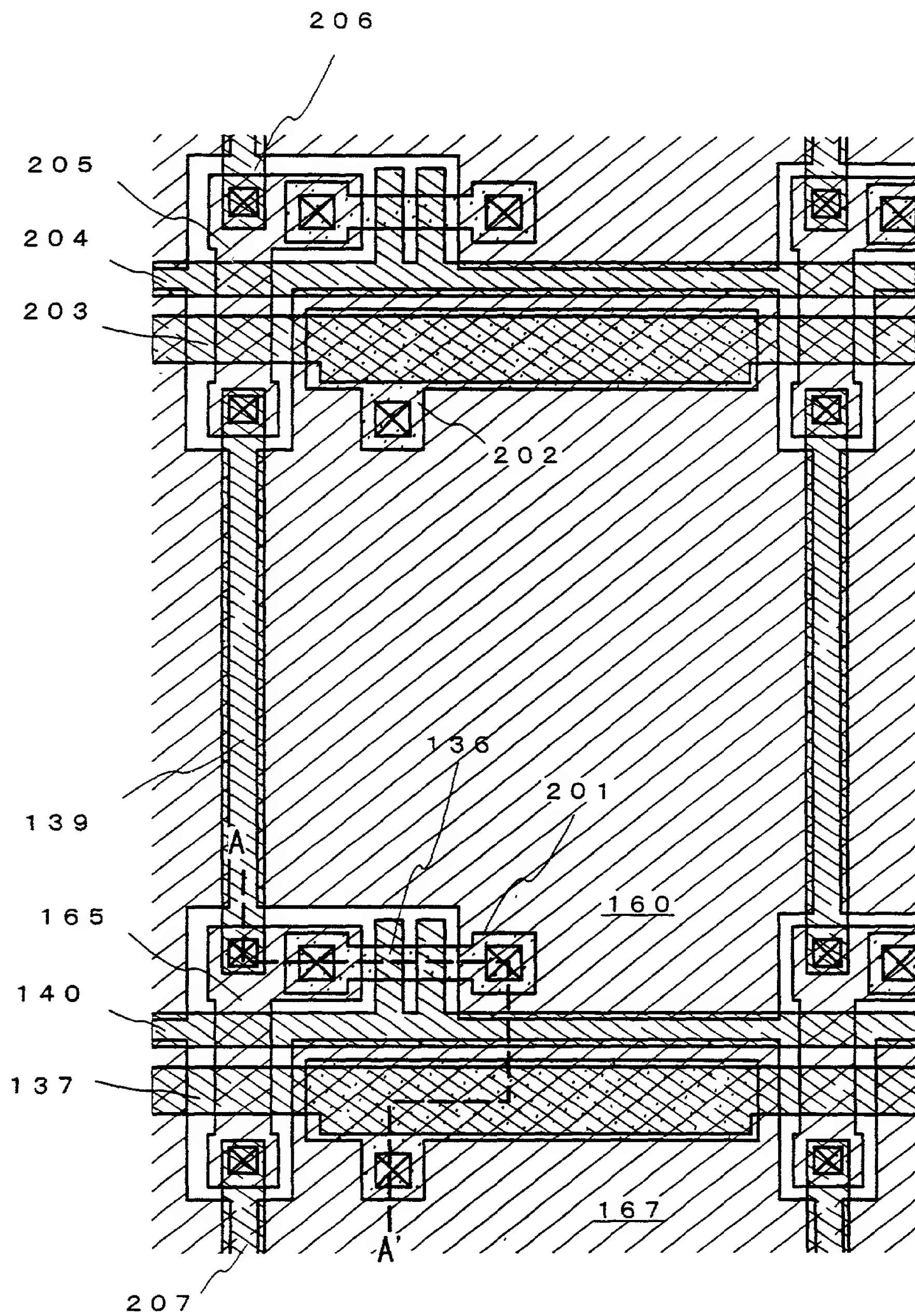
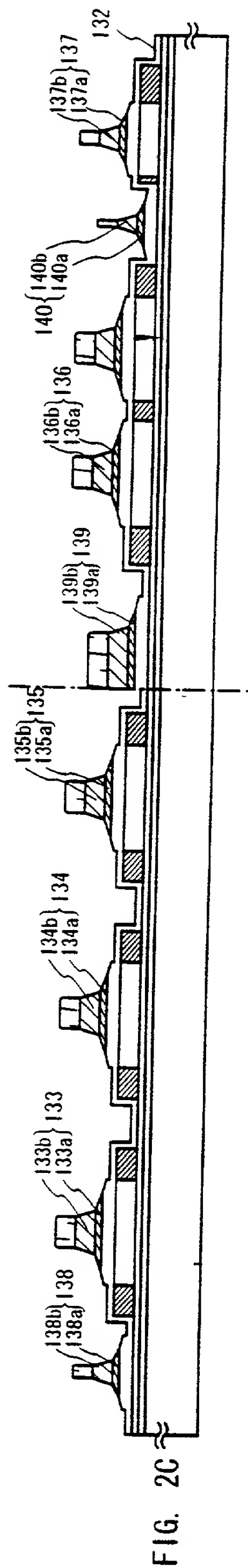
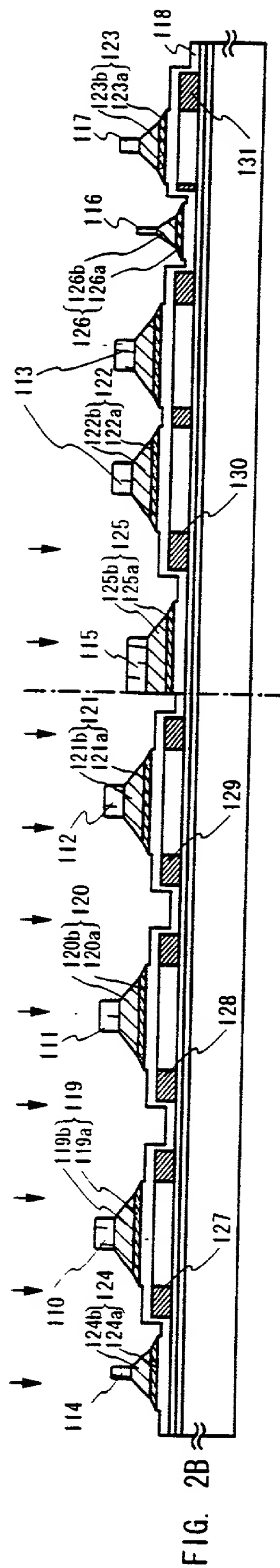
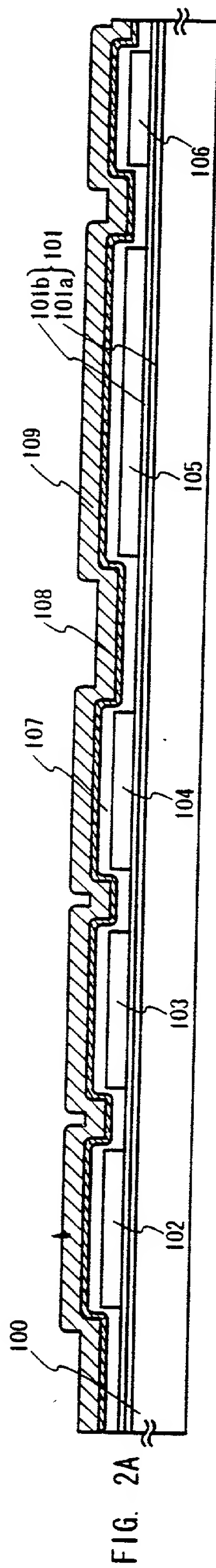


FIG. 1



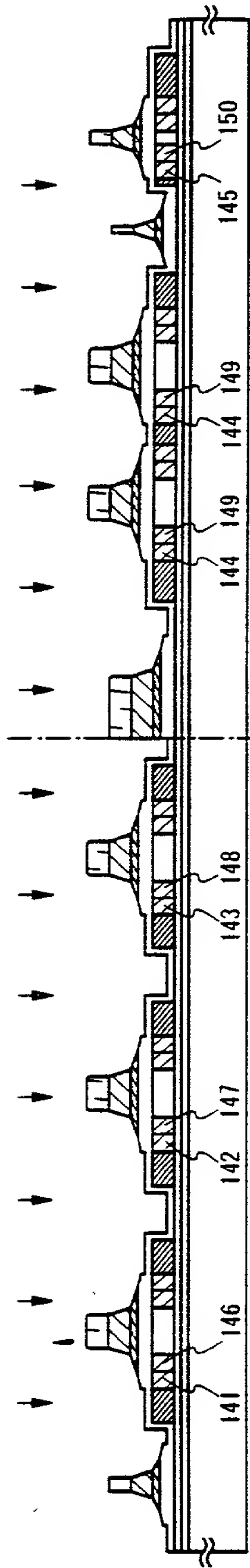


FIG. 3A

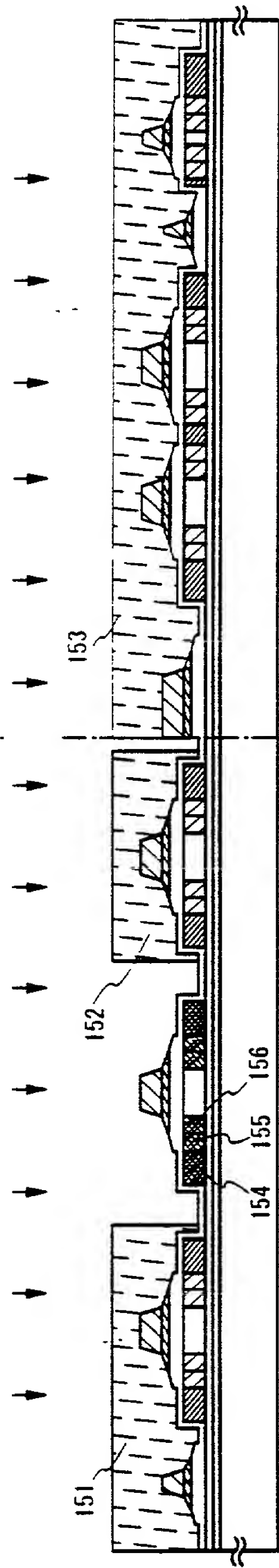


FIG. 3B

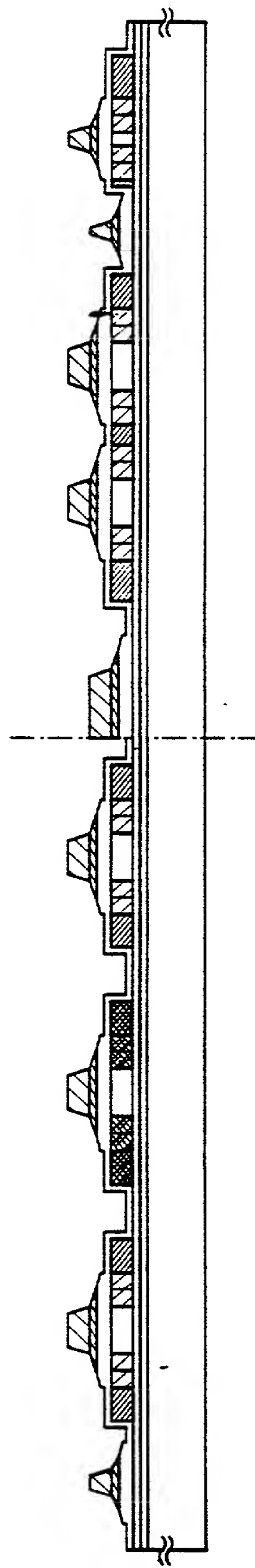


FIG. 3C

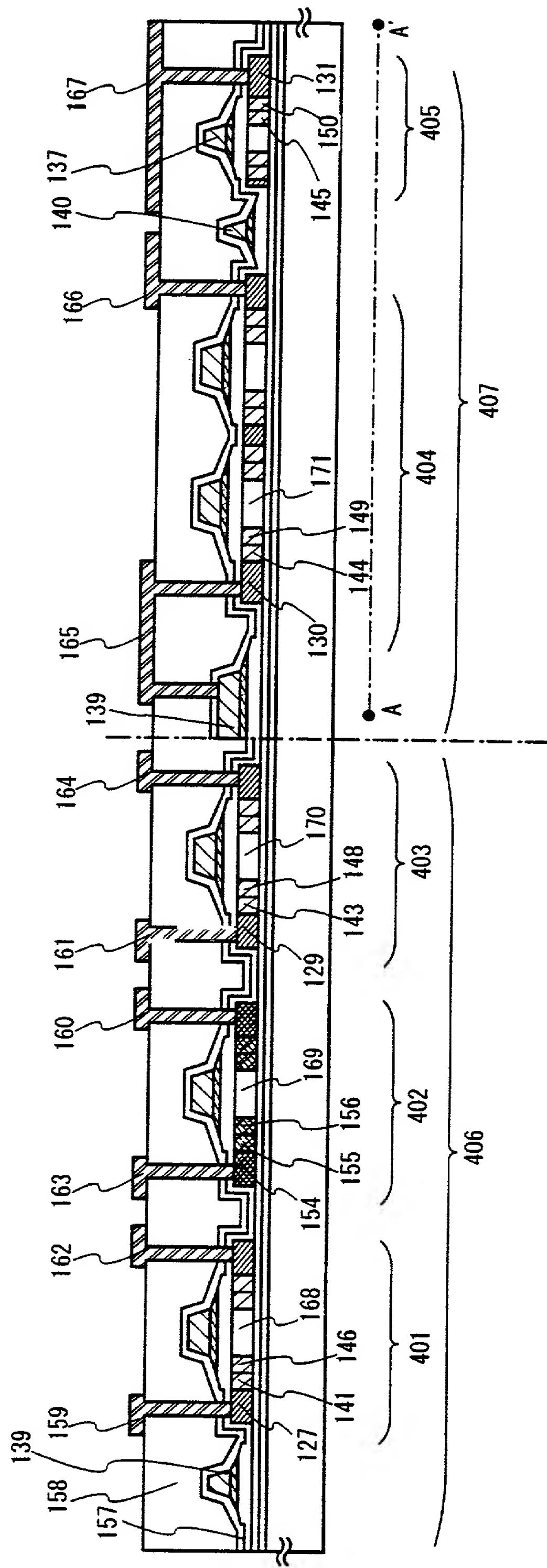


FIG. 4

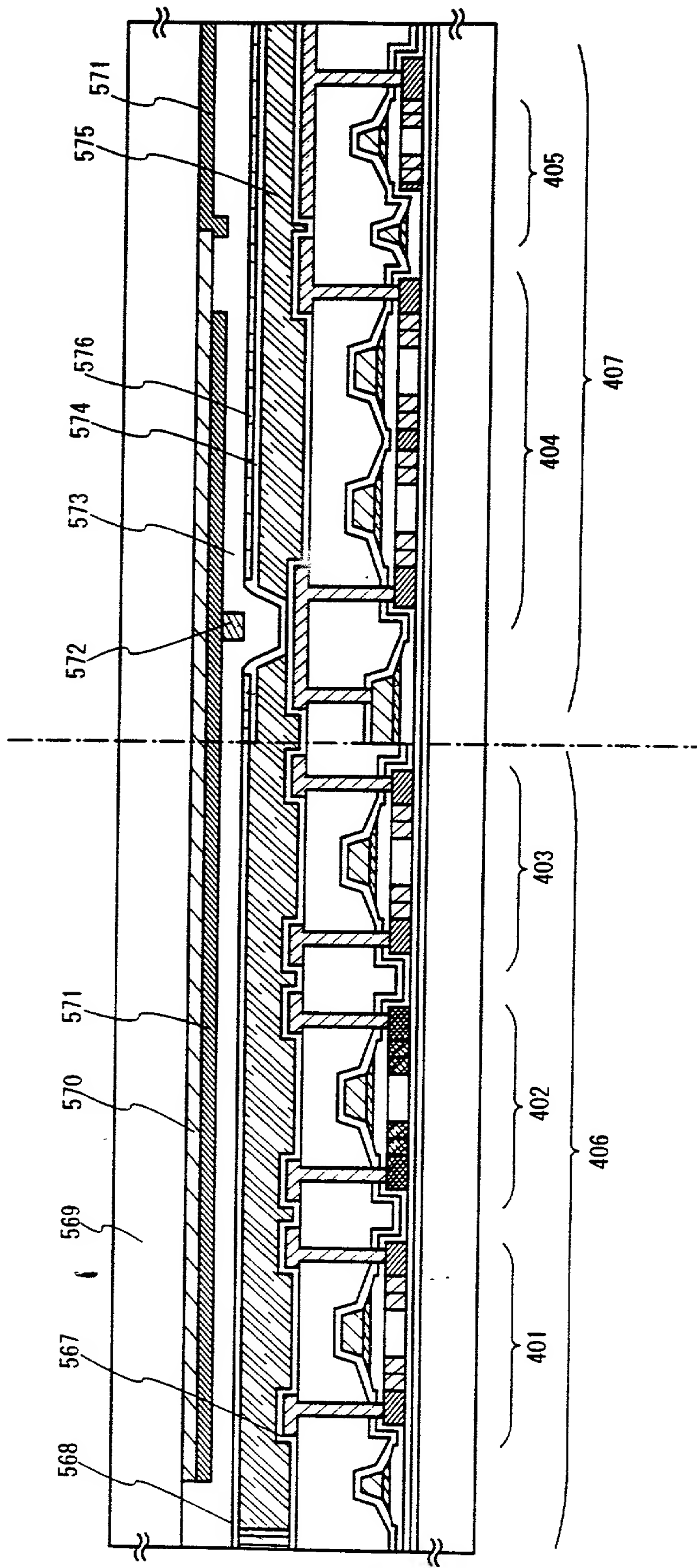


FIG. 5

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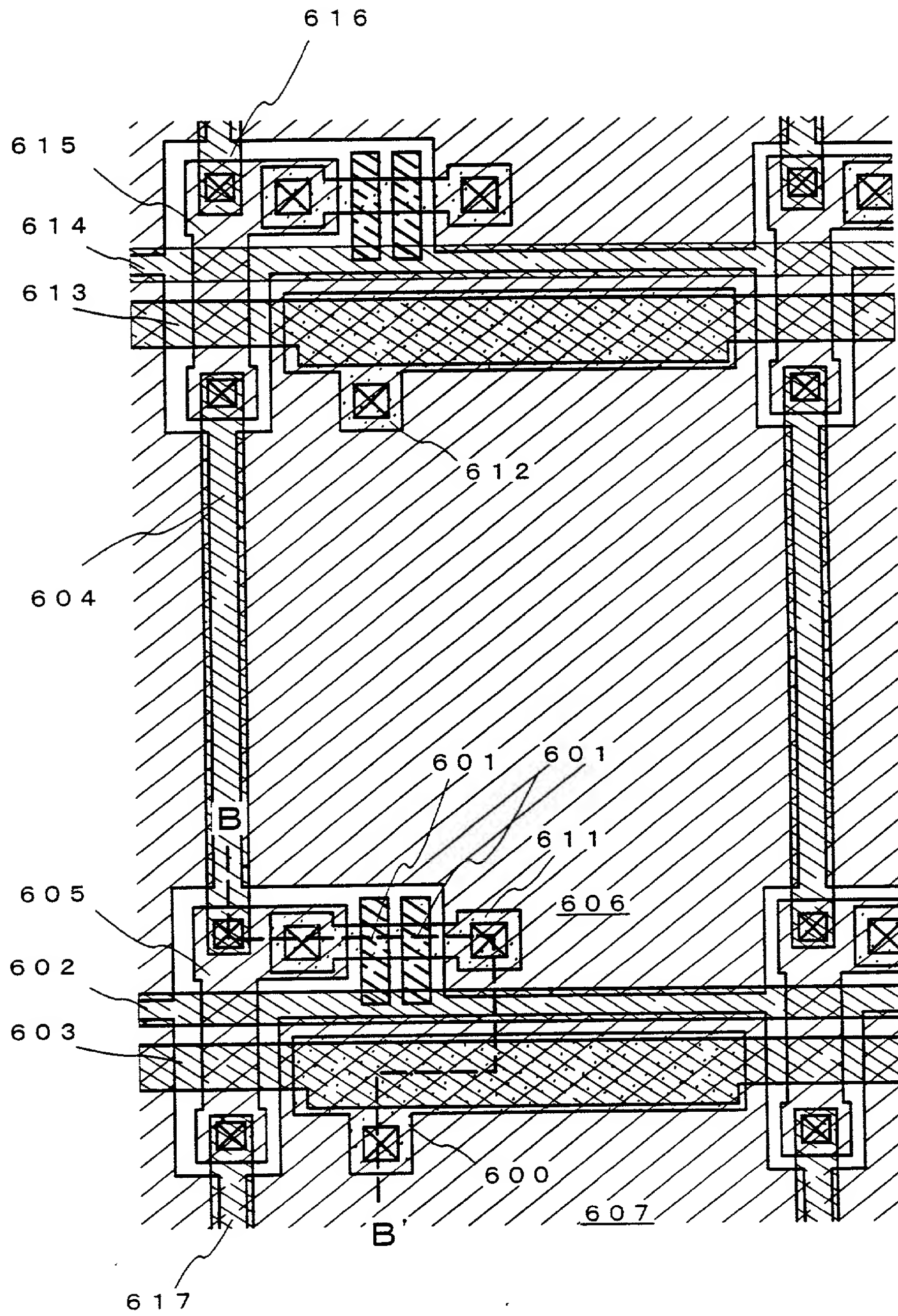


FIG. 6

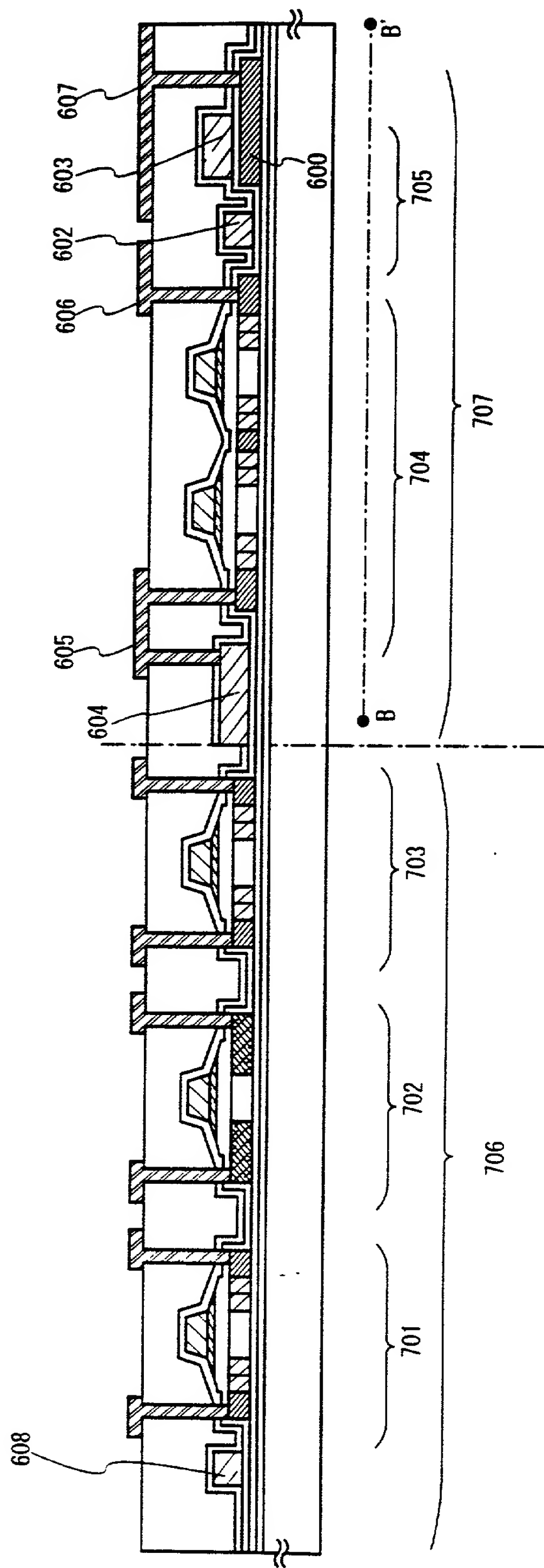


FIG. 7

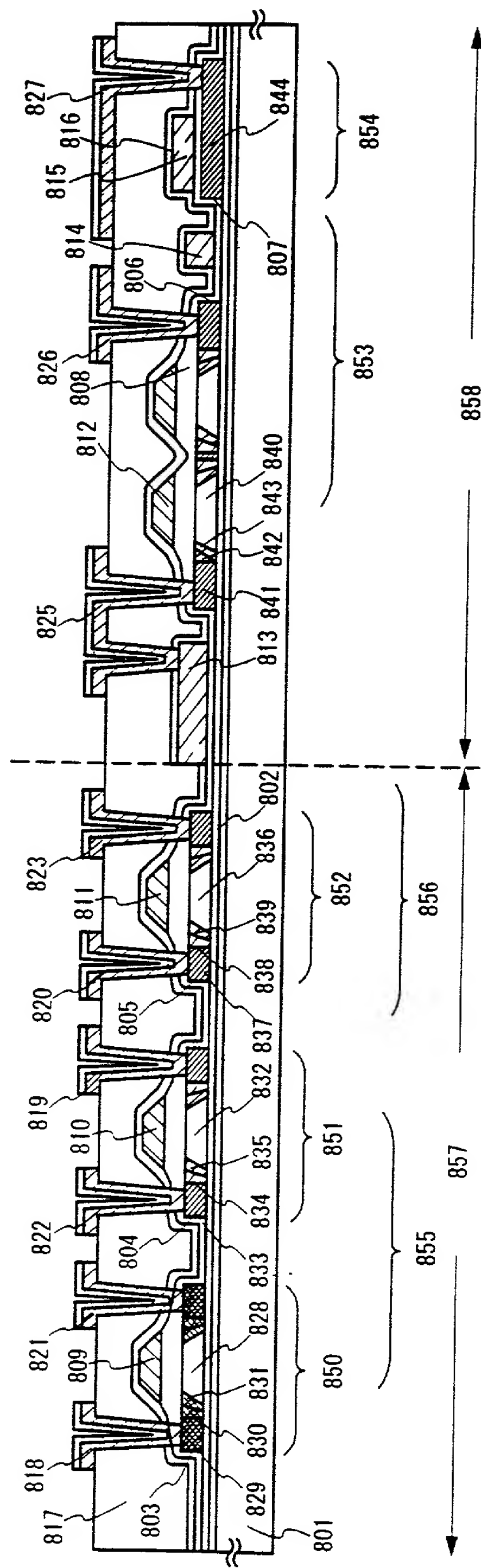


FIG. 8

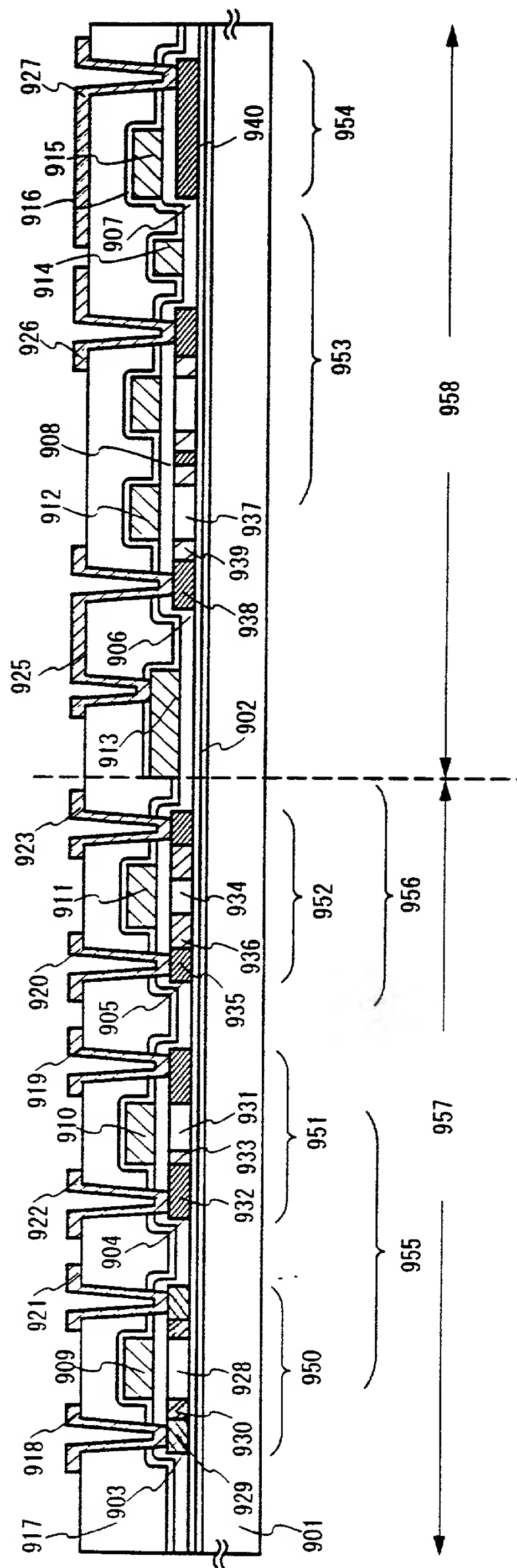


FIG. 9

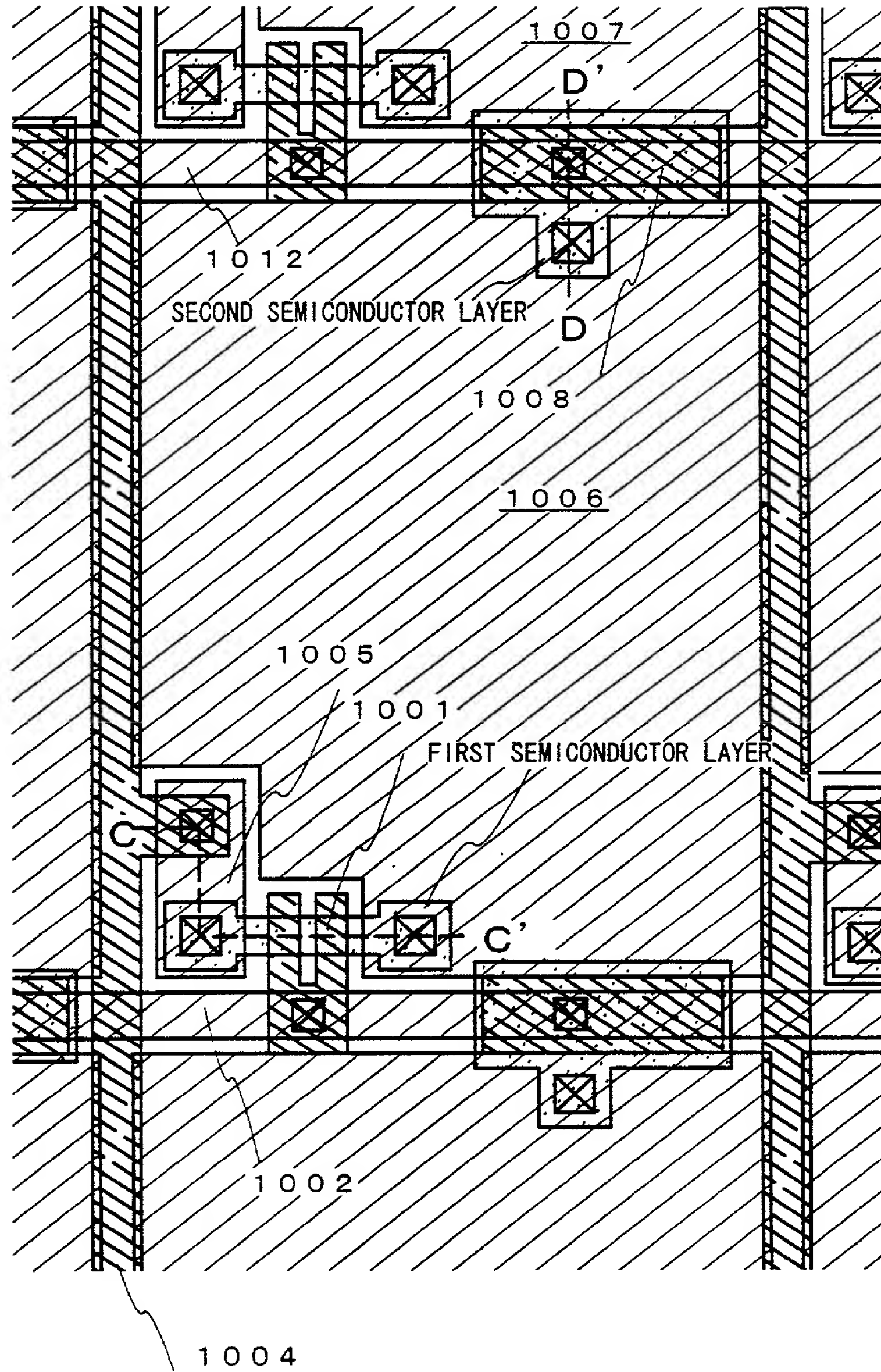


FIG. 10

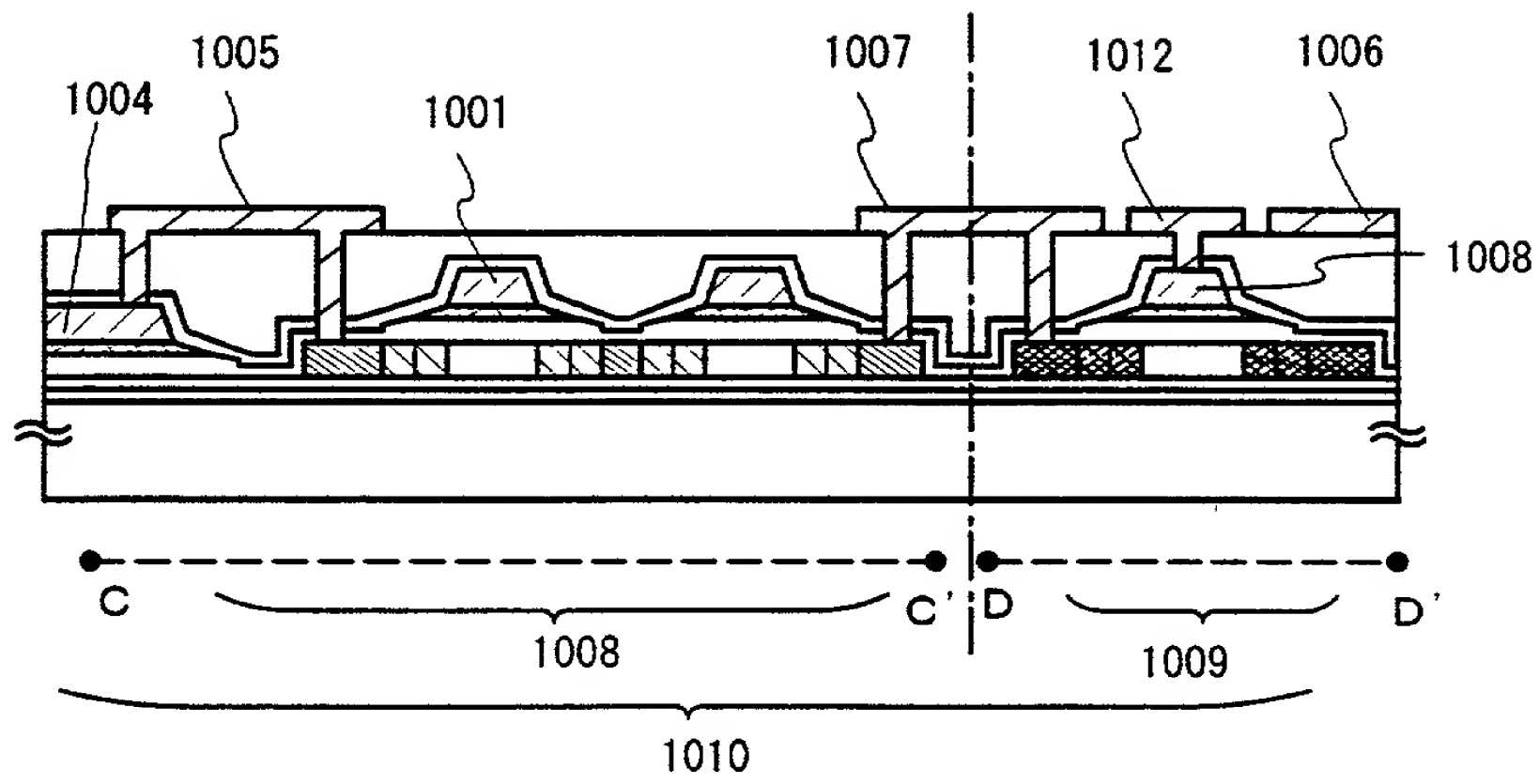


FIG. 11

This diagram shows a cross-sectional view of a semiconductor device. It features a top layer with a grid of rectangular openings. Below these openings are vertical structures, some of which are filled with a hatched material. At the base of these structures are conical features. The diagram is labeled with various reference numerals: 1116, 1113, 1112, 1114, 1109, 1111, and 1110. The bottom of the diagram is marked with 'E' and 'E'.

FIG. 12B

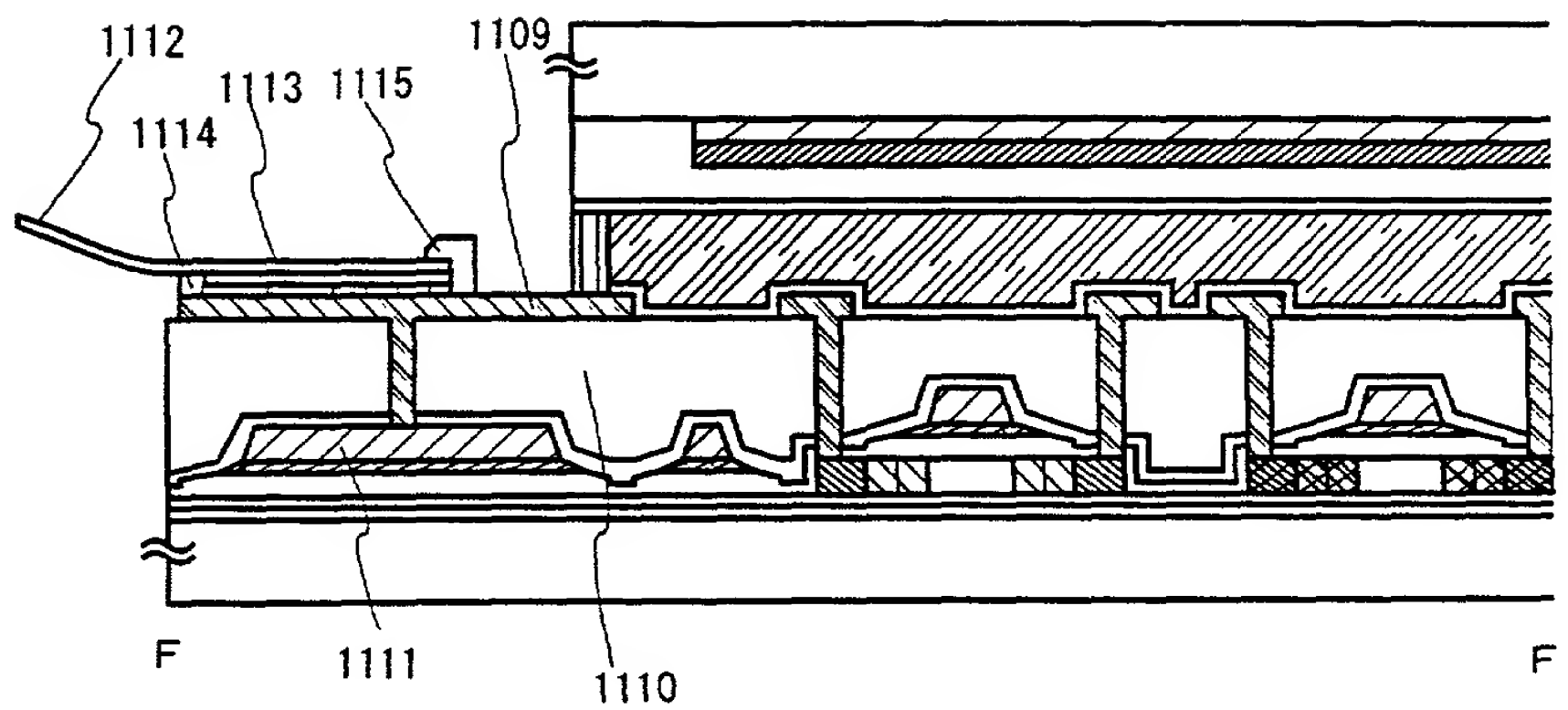


FIG. 13A

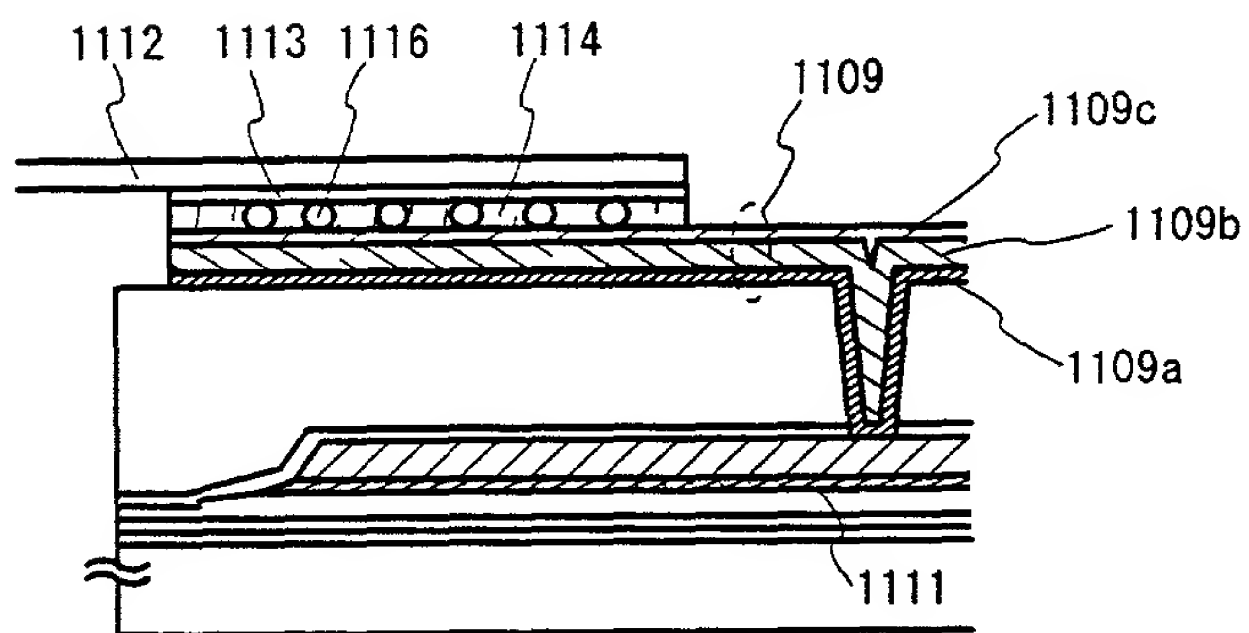


FIG. 13B

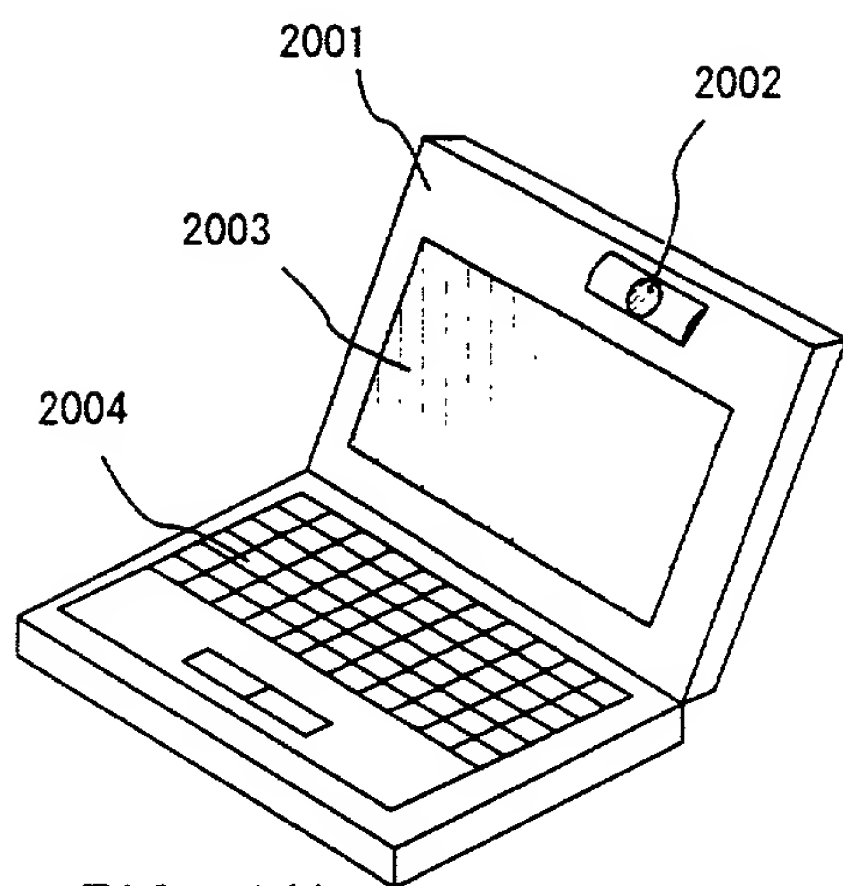


FIG. 14A

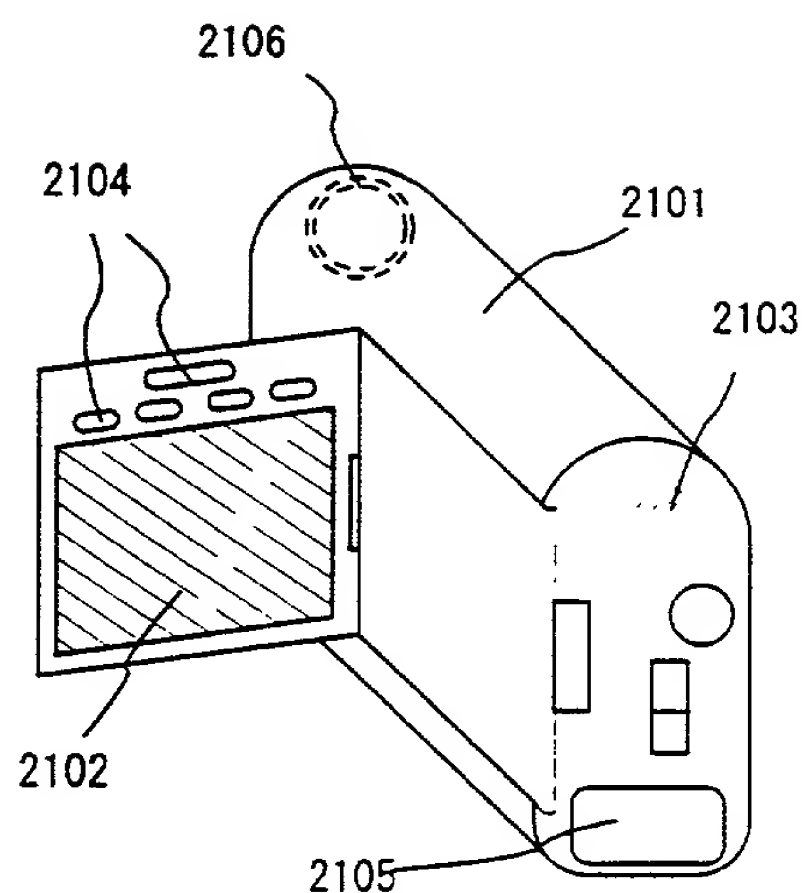


FIG. 14B

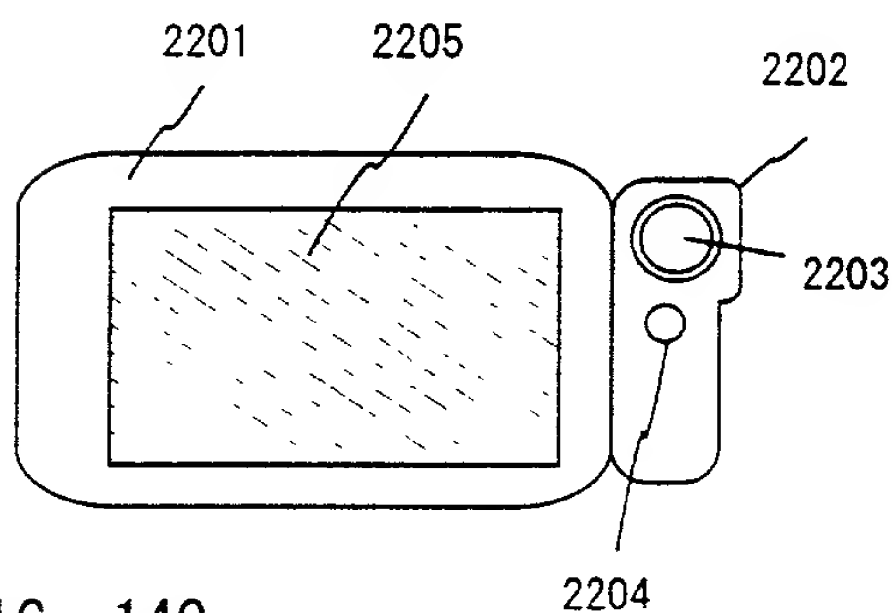


FIG. 14C

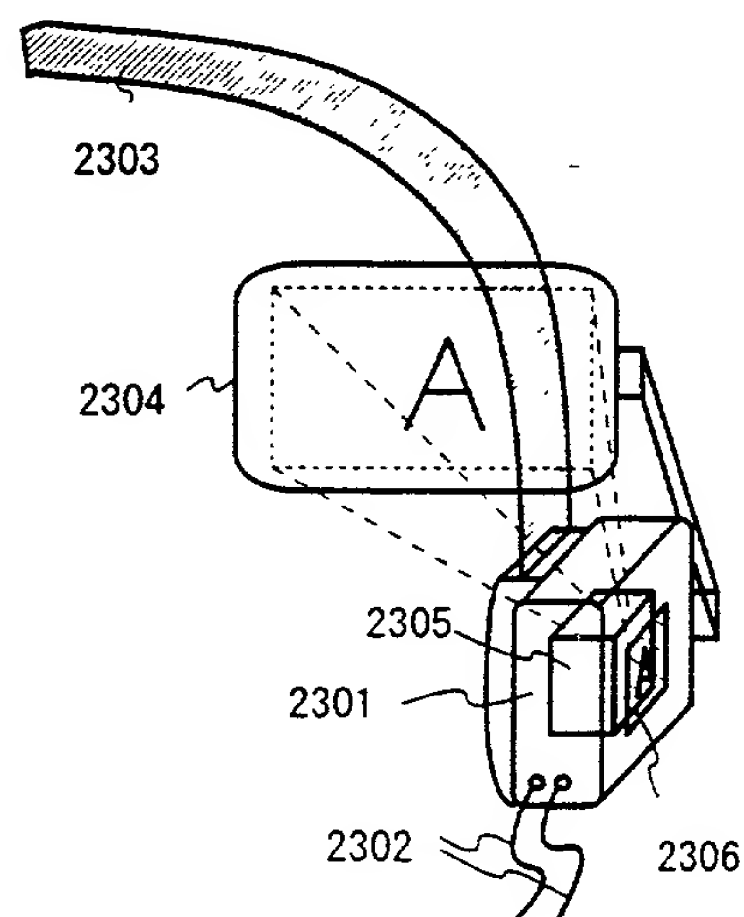


FIG. 14D

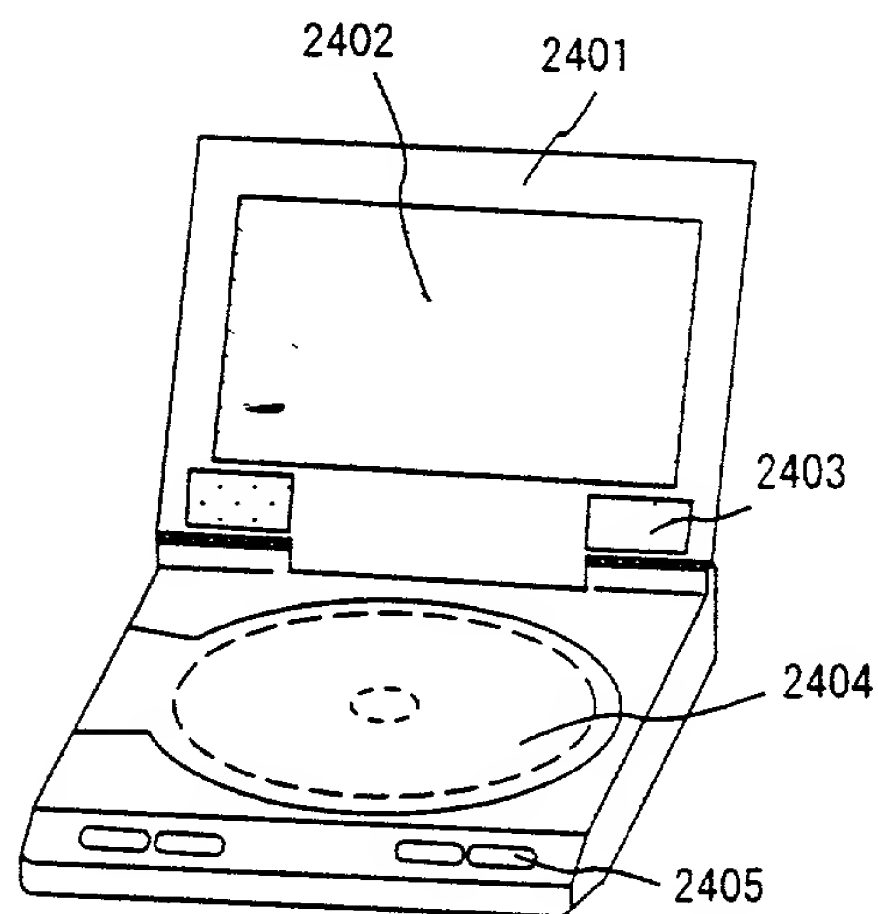


FIG. 14E

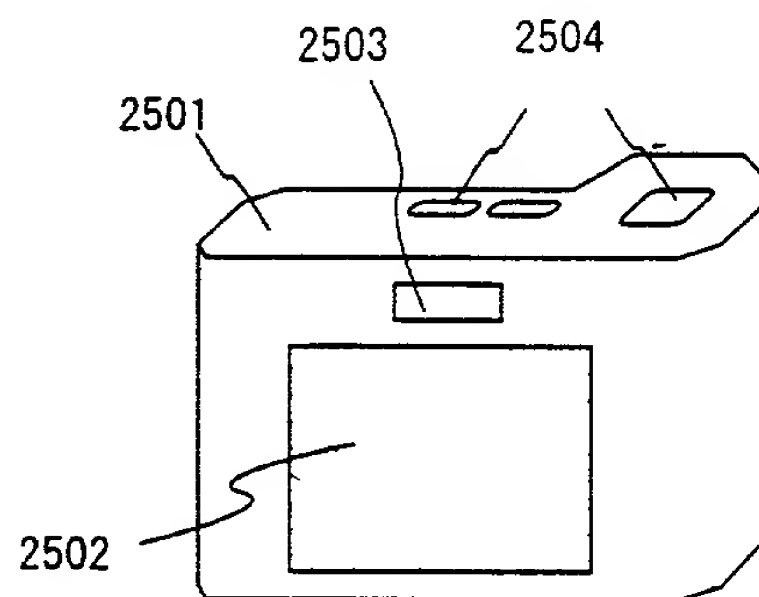


FIG. 14F

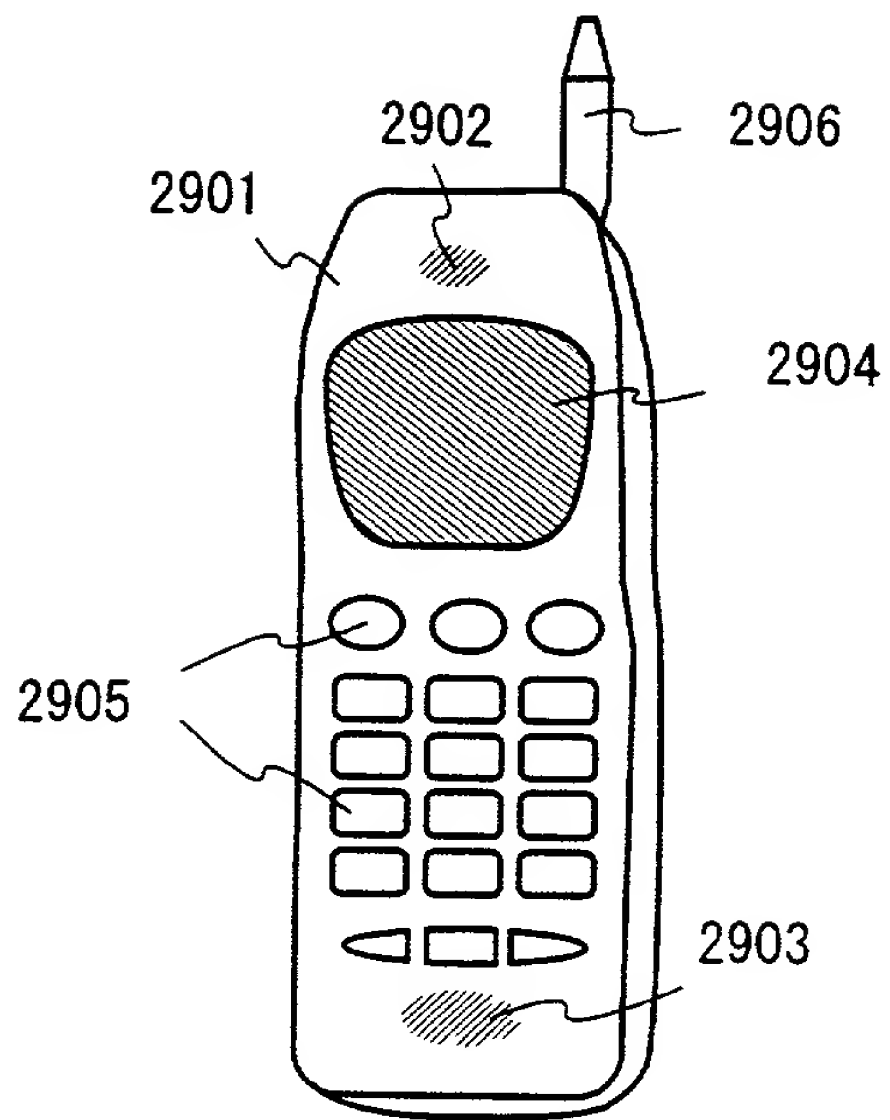


FIG. 15A

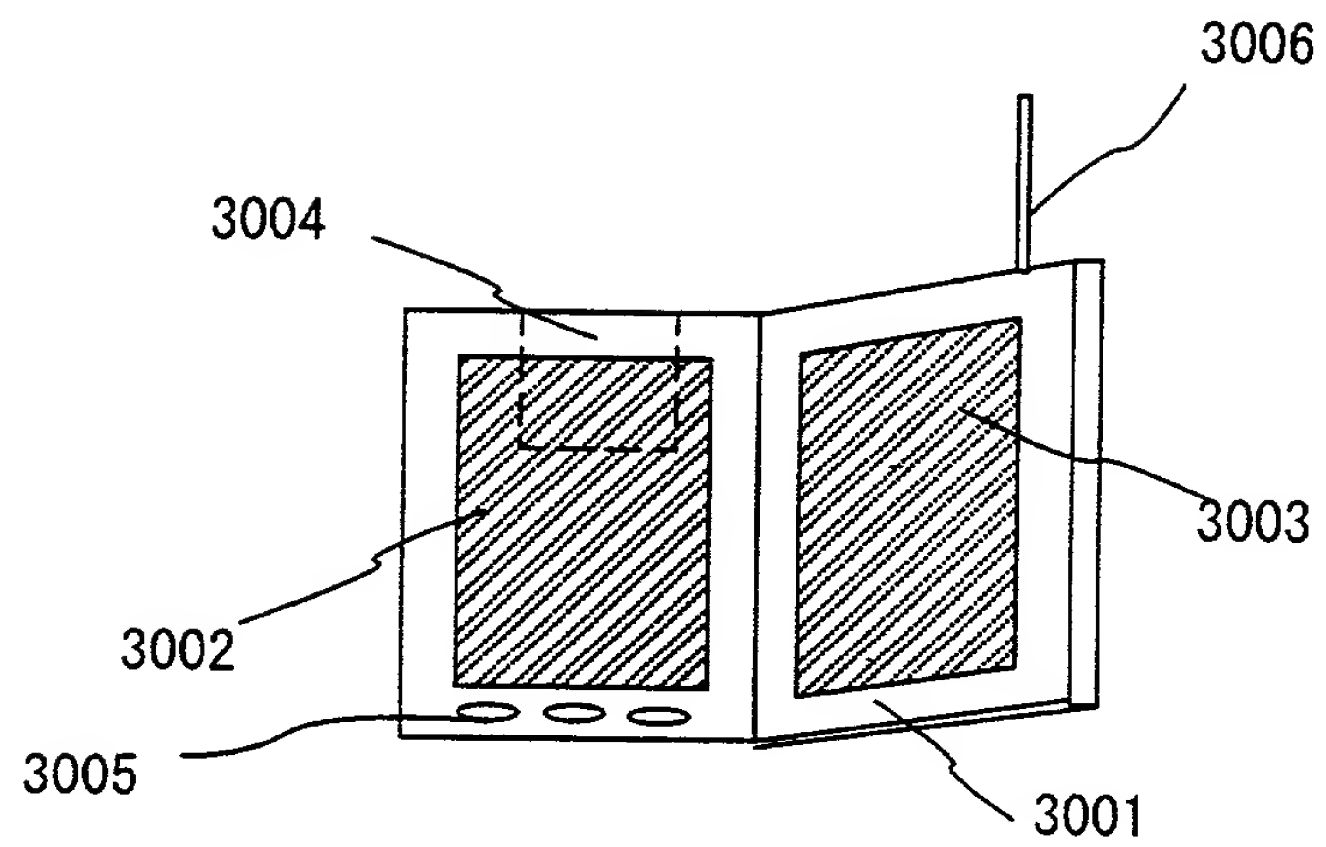


FIG. 15B

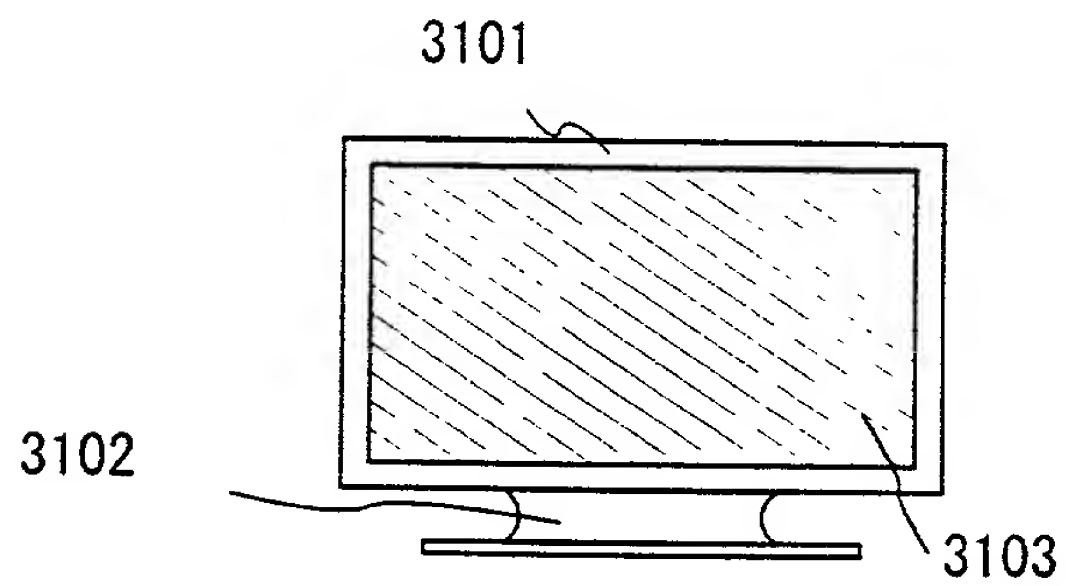


FIG. 15C

